CNA1012K (ON1114)

Photo Interrupter

For contactless SW and object detection

Overview

CNA1012K is a photocoupler in which a high efficiency GaAs infrared light emitting diode is used as the light emitting element, and a high sensitivity phototransistor is used as the light detecting element. The two elements are arranged so as to face each other, and objects passing between them are detected.

■ Features

- Highly precise position detection: 0.3 mm
- Wide gap between emitting and detecting elements, suitable for thick plate detection
- Fast response: t_r , $t_f = 6 \mu s$ (typ.)
- Small output current variation against change in temperature
- Large output current

■ Absolute Maximum Ratings $T_a = 25 \Sigma \Delta \gamma \rho C$

F	Symbol	Rating	Unit		
	Power dissipation *1	P _D	75	mW	
Input (Light emitting diode)	Forward current	I_{F}	50	mA	
	Reverse voltage V _R 3		3	V	
Output (Photo transistor)	Collector-emitter voltage (Base open)	V _{CEO}	V _{CEO} 30		
	Emitter-collector voltage (Base open)	V _{ECO}	5 5 101	V	
	Collector current	$I_{\rm C}$	20	mA	
	Collector power dissipation *2	$P_{\rm C}$	100	mW	
Operating ambient temp	Topr	-25 to +85	°C		
Storage temperature	T _{stg}	-30 to +100	°C		

Note) *1: Input power derating ratio is 1.0 mW/°C at $T_a \ge 25$ °C.

■ Electrical-Optical Characteristics $T_a = 25\Sigma\Delta\gamma\rho C \pm 3\Sigma\Delta\gamma\rho C$

Parameter		Symbol	Conditions	Min	Тур	Max	Unit
Input characteristics	Reverse current	I_R	$V_R = 3 V$			10	μΑ
	Forward voltage	$V_{\rm F}$	$I_F = 50 \text{ mA}$		1.2	1.5	V
Output characteristics	Collector-emitter cutoff current (Base open)	I _{CEO}	$V_{CE} = 10 \text{ V}$			200	nA
	Collector-emitter capacitance	C _C	$V_{CE} = 10 \text{ V, } f = 1 \text{ MHz}$		5		pF
Transfer characteristics	Collector current	$I_{\rm C}$	$V_{CE} = 10 \text{ V}, I_F = 20 \text{ mA}$	0.7			mA
	Collector-emitter saturation voltage	V _{CE(sat)}	$I_F = 50 \text{ mA}, I_C = 0.1 \text{ mA}$			0.3	V
	Rise time *	t _r	$V_{CC} = 10 \text{ V}, I_{C} = 1 \text{ mA},$		6.0		μs
	Fall time *	$t_{\rm f}$	$R_L = 100 \Omega$		6.0		μs

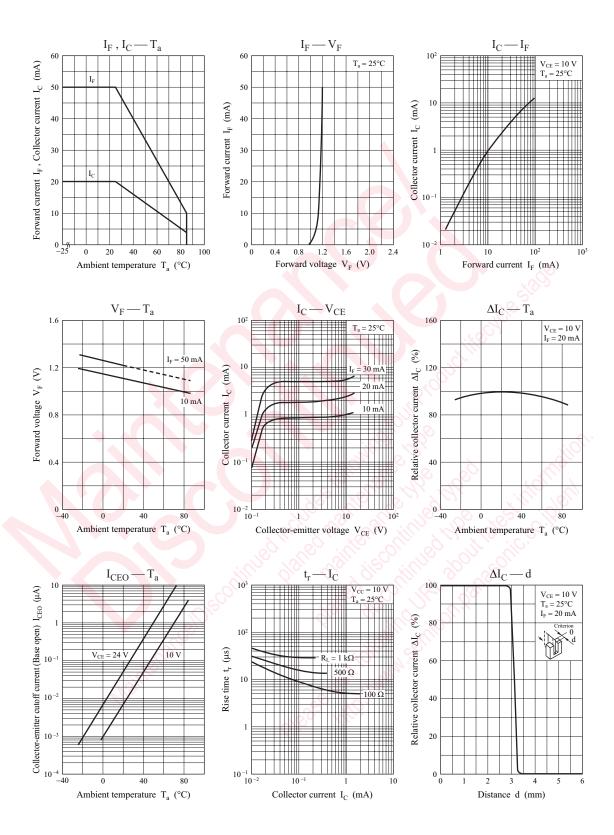
Note) 1. Input and output are practiced by electricity.

2. This device is designed by disregarding radiation.



^{*2:} Output power derating ratio is 1.34 mW/°C at $T_a \ge 25$ °C.

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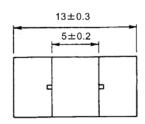


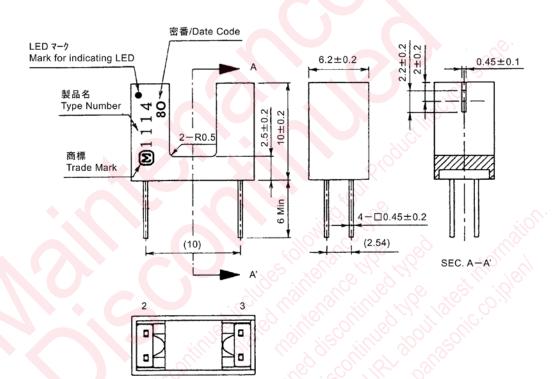
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■ Package (Unit: mm)

LSSSIR4S0005





(注 1) マークは、目視又は顕微鏡に於いて解読できる事。 (Note1) The marks can be identified either with eyes or a microscope.

- Pin name
 - 1: Anode
 - 2: Cathode
 - 3: Collector
 - 4: Emitter

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